

AMENDMENTS TO THE SPECIFICATION

On page 3, please amend paragraph [12] as follows:

The present invention addresses and solves problems attendant upon fabricating miniaturized semiconductor devices, particularly transistors having a miniaturized gate electrode, such as a gate electrode with a height less than 1,000 Å and a width less than 500 Å. Conventional photolithographic techniques are limited in their ~~ability~~ resolution capabilities and, hence, cannot be used to pattern gate electrodes with a width less than 500 Å with the requisite precision and reproducibility. Reduction of the gate width disadvantageously increases the aspect ratio of the gate electrode. However, the gate electrode must be sufficiently ~~sufficiently~~ high to prevent implanted impurities from penetrating therethrough into the underlying gate oxide layer with attendant degradation thereof, as during ion implantation to form deep source/drain regions.